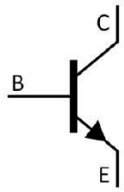
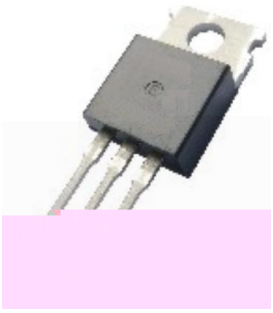
Silicon NPN transistor in a TO-220 Plastic Package.

High DC current gain, low saturation voltage, high power dissipation, complementary to 2SB834.

Audio frequency power amplifier applications.



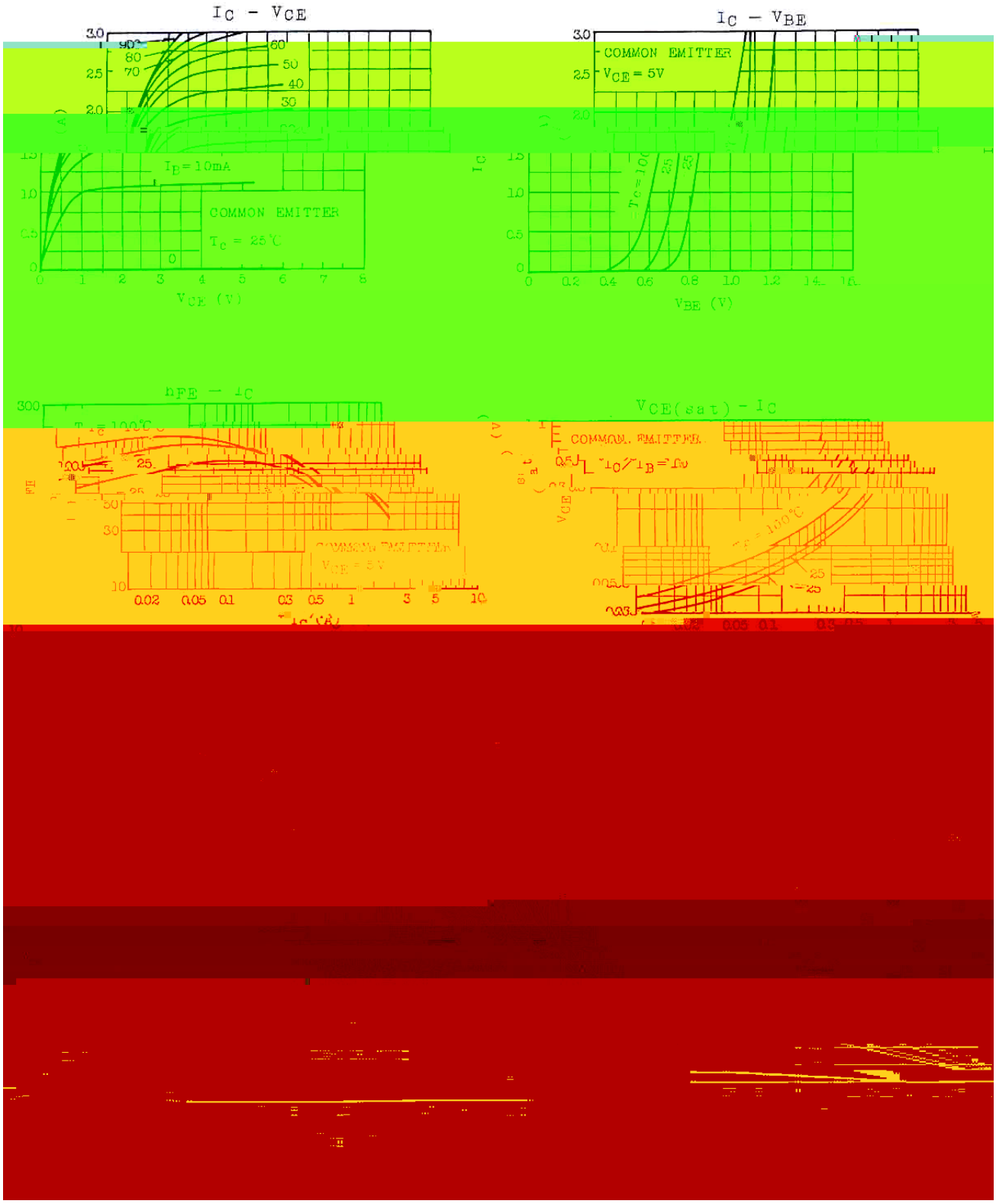


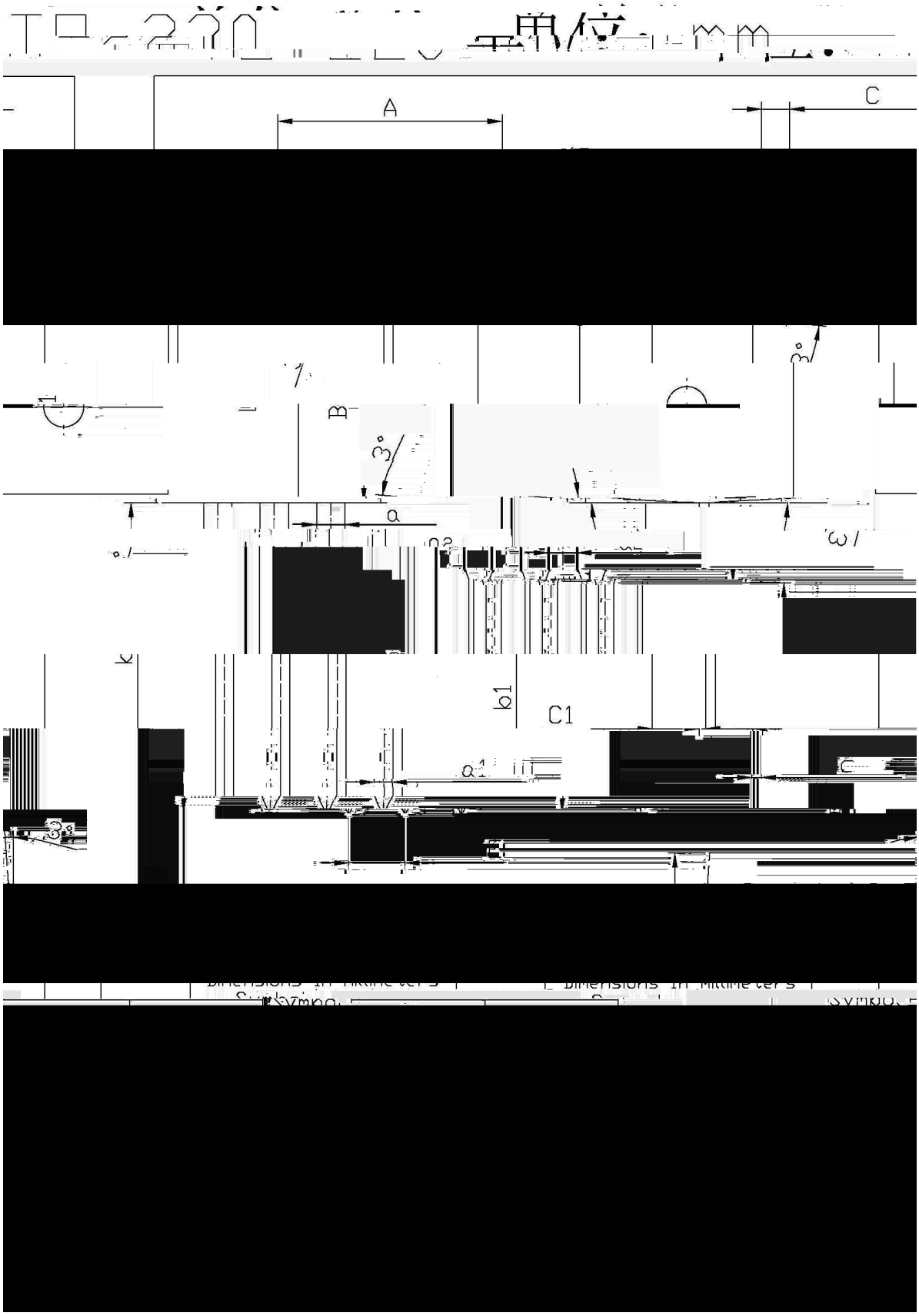
PIN1 Base PIN 2 Collector PIN 3 Emitter

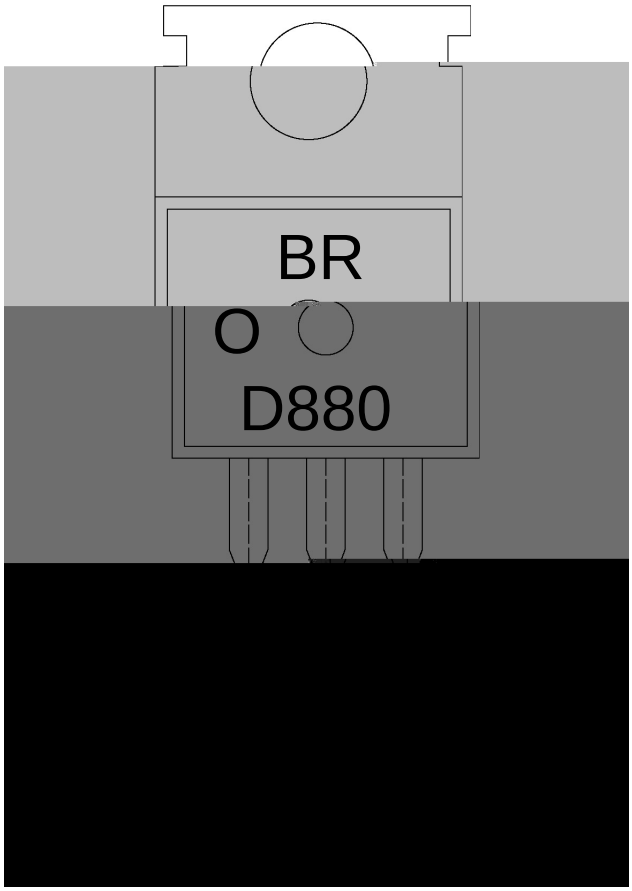
h_{FE} Classifications Symbol	O	Y	GR
h_{FE} Range	60 120	100 200	150 300

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	3.0	A
Base Current - Continuous	I_B	0.5	A
Collector Power Dissipation	P_C	1.5	W
	$P_C(T_C=25$)	30	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=50mA I_B=0	60			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=60V I_E=0			100	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=7.0V I_C=0			100	μA


IC - VCE
IB = 10mA
COMMON EMITTER
TC = 25°C
VCE (V)
IC - VBE
COMMON EMITTER
VCE = 5V
VBE (V)
hFE - IC
VCE(sat) - IC
COMMON EMITTER


A
C
B
a
b1
C1



BR

D880

h_{FE}

Note:

BR:	Company Code
D880:	Product Type.
O:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.